

# **RF AMPLIFIER**

## **MODEL TM9702**

**Available as:** TN9702, 4 Pin Surface Mount (SM3)  
BX9702, Connectorized Housing (H1)

## Features

- GaAs FET; Medium Gain: 12 dB Typical
  - High Output Power: +20dBm Typical

## Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -55 °C to +85 °C	
Frequency	500 - 1500 MHz	500 - 1500 MHz	
Gain (dB)	12	10.5 Min.	
Power @ 1 dB Comp. (dBm)	+20	+19.0	Min.
Reverse Isolation (dB)	- 18	- 16	Max.
VSWR	In	<1.5:1	2.0:1 Max.
	Out	<1.5:1	2.0:1 Max.
Noise figure (dB)	3.0	4.5	Max.
Power	Vdc	+8	+8
	mA	105	110 Max.

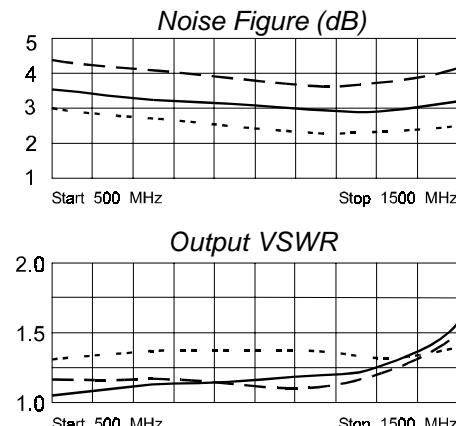
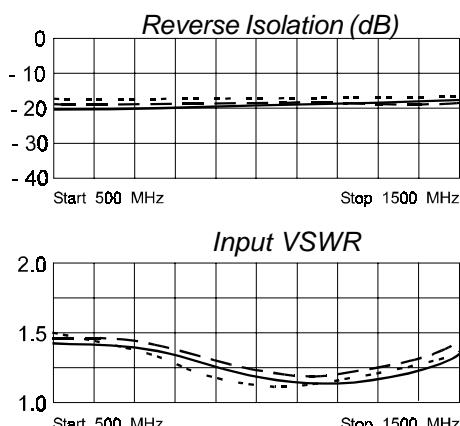
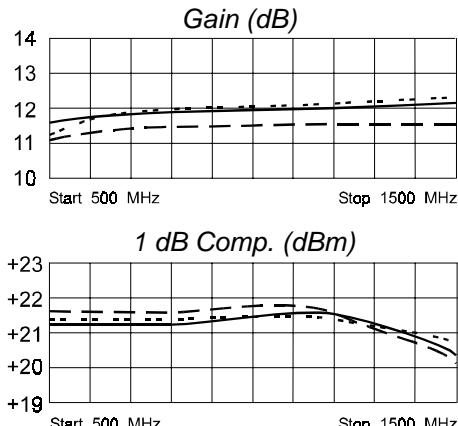
Note: Care should always be taken to effectively ground the case of each unit.

## Typical Intermodulation Performance at 25 ° C

Second Order Harmonic Intercept Point ..... +46 (Typ.)  
 Second Order Two Tone Intercept Point ..... +40 (Typ.)  
 Third Order Two Tone Intercept Point ..... +31 (Typ.)

## Maximum Ratings

Ambient Operating Temperature .....	-55°C to + 100 °C
Storage Temperature .....	-62°C to + 125 °C
Case Temperature .....	+ 125 °C
DC Voltage .....	+ 10 Volts
Continuous RF Input Power .....	+ 20 dBm
Short Term RF Input Power .....	200 Milliwatts (1 Minute Max.)
Maximum Peak Power .....	0.5 Watt 3 usec Max.)



## Linear S-Parameters

FREQ. MHz	S11---		S21---		S12---		S22--	
	Mag	Deg	Mag	Deg	Mag	Deg	Mag	Deg
300	.19	- 20	3.61	172	.09	- 1	.07	62
500	.17	- 18	374	148	.10	- 18	.02	177
700	.14	- 29	3.97	127	.10	- 34	.07	170
900	.08	43	3.99	106	.10	- 48	.10	139
1100	.02	-174	3.97	94	.11	- 68	.10	104
1300	.11	132	3.79	61	.11	- 97	.07	53
1500	.23	121	3.63	38	.11	-108	.09	- 46

# Amplifonix

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